

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		<small>Complete if Known</small>	
		Application Number	10/602,315
		Filing Date	June 24, 2003
		First Named Inventor	Ahn, Kie
		Group Art Unit	2829
		Examiner Name	Sarkar, Asok
Sheet 1 of 1		Attorney Docket No: 1303.107US1	

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EXAMINER

Asok Kumar Sarkar

DATE CONSIDERED

4/29/05